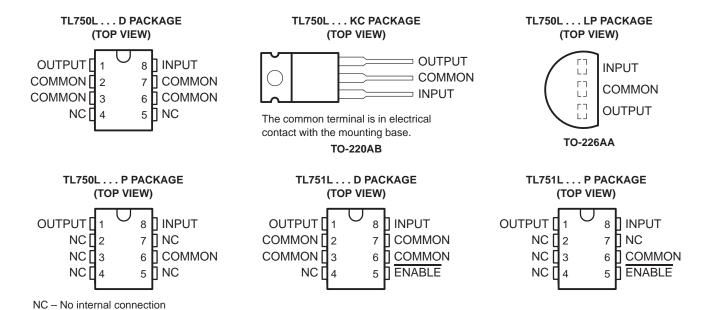
- Very Low Dropout Voltage, Less Than 0.6 V at 150 mA
- Very Low Quiescent Current
- TTL- and CMOS-Compatible Enable on TL751L Series
- 60-V Load-Dump Protection

- Reverse Transient Protection Down to –50 V
- Internal Thermal-Overload Protection
- Overvoltage Protection
- Internal Overcurrent-Limiting Circuitry
- Less Than 500-μA Disable (TL751L Series)



DEVICE COMPONENT COUNT		
Transistors	20	
JFETs	2	
Diodes	5	
Resistors	16	

#### description

The TL750L and TL751L series are low-dropout positive-voltage regulators specifically designed for battery-powered systems. These devices incorporate overvoltage and current-limiting protection circuitry, along with internal reverse-battery protection circuitry to protect the devices and the regulated system. The series is fully protected against 60-V load-dump and reverse-battery conditions. Extremely low quiescent current during full-load conditions makes these devices ideal for standby power systems.

The TL750L and TL751L series of fixed-output voltage regulators offers 5-V, 8-V, 10-V, and 12-V options. The TL751L series has the addition of an enable (ENABLE) input. When ENABLE is high, the regulator output is placed in the high-impedance state. This gives the designer complete control over power up, power down, or emergency shutdown.



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#### description (continued)

The TL750LxxC and the TL751LxxC series are characterized for operation over the virtual junction temperature range of 0°C to 125°C. The TL750L05Q and TL751L05Q are characterized for operation over the virtual junction temperature range of -40°C to 125°C.

#### **AVAILABLE OPTIONS**

	V <sub>O</sub> TYP		PA	CKAGED DEVICE	S	
TJ	AT 25°C	SMALL OUTLINE (D)	HEAT-SINK MOUNTED (KC)	PLASTIC CYLINDRICAL (LP)	PLASTIC DIP (P)	CHIP FORM (Y)
	5 V	TL750L05CD TL751L05CD	TL750L05CKC	TL750L05CLP	TL750L05CP TL751L05CP	TL750L05Y
0°C to 125°C	8 V	TL750L08CD TL751L08CD	TL750L08CKC	TL750L08CLP	TL750L08CP TL751L08CP	TL750L08Y
0 0 10 125 0	10 V	TL750L10CD TL751L10CD	TL750L10CKC	TL750L10CLP	TL750L10CP TL751L10CP	TL750L10Y
	12 V	TL750L12CD TL751L12CD	TL750L12CKC	TL750L12CLP	TL750L12CP TL751L12CP	TL750L12Y
-40°C to 125°C	5 V	TL750L05QD TL751L05QD	-	-	-	-

The D, KTE, and LP packages are available taped and reeled. The KTP is only available taped and reeled. Add R suffix to device type (e.g., TL750L05CDR). Chip forms are tested at 25°C.

#### absolute maximum ratings over operating junction temperature range (unless otherwise noted)

		TL750Lxx TL751Lxx	UNIT	
Continuous input voltage		26	V	
Transient input voltage, T <sub>A</sub> = 25°C (see Note 1)		60	V	
Continuous reverse input voltage			V	
Transient reverse input voltage: t ≤ 100 ms	-50	V		
	D package	97		
Package thermal impedance, θ,ιΔ (see Notes 2 and 3)	KC package	22	°C	
Package merman impedance, θηλ (see Notes 2 and 3)	LP package	156		
	P package	127		
Virtual junction temperature range, TJ		-40 to 150	°C	
Lead temperature 1,6 mm (1/16 inch) for 10 seconds		260	°C	
Storage temperature range, T <sub>stg</sub>		-65 to 150	°C	

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The transient input voltage rating applies to the waveform shown in Figure 1.

- 2. Maximum power dissipation is a function of T<sub>J</sub>(max), θ<sub>JA</sub>, and T<sub>A</sub>. The maximum allowable power dissipation at any allowable ambient temperature is  $P_D = (T_J(max) - T_A)/\theta_{JA}$ . Operating at the absolute maximum  $T_J$  of 150°C can impact reliability.
- The package thermal impedance is calculated in accordance with JESD 51, except for through-hole packages, which use a trace length of zero.



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# recommended operating conditions over recommended operating junction temperature range (unless otherwise noted)

			MIN	MAX	UNITS
		TL75xL05	6	26	
Innut voltage V	Institution N		9	26	V
<b>.</b>		TL75xL10	11	26	V
		TL75xL12	13	26	
High-level ENABLE input voltage, VIH		TL751Lxx	2	15	V
Low local FMARI E income No. #	T <sub>A</sub> = 25°C	TL751Lxx	-0.3	0.8	V
Low-level ENABLE input voltage, V <sub>IL</sub> †	T <sub>A</sub> = full range‡	TL751Lxx	-0.15	0.8	V
Output current range, IO		TL75xLxx	0	150	mA
Operation similar investigation termonature. To		TL75xLxxC	0	125	°C
Operating virtual junction temperature, T <sub>J</sub>		TL75xL05Q	-40	125	

<sup>†</sup> The algebraic convention, in which the least positive (most negative) value is designated minimum, is used in this data sheet for ENABLE voltage levels and temperature only.

### electrical characteristics, $V_I = 14 \text{ V}$ , $I_O = 10 \text{ mA}$ , $T_J = 25^{\circ}\text{C}$ (unless otherwise noted) (see Note 4)

PARAMETER TEST CONDITIONS§		TL750L05 TL751L05			UNIT
		MIN	TYP	MAX	
Output voltage		4.80	5	5.2	V
Output voltage	$T_J = T_J(min)$ to 125°C¶	4.75		5.25	V
Input regulation voltage	V <sub>I</sub> = 9 V to 16 V		5	10	mV
Input regulation voltage	V <sub>I</sub> = 6 V to 26 V		6	30	IIIV
Ripple rejection	V <sub>I</sub> = 8 V to 18 V, f = 120 Hz	60	65		dB
Output regulation voltage	I <sub>O</sub> = 5 mA to 150 mA		20	50	mV
Dropout voltage	$I_O = 10 \text{ mA}$			0.2	V
Dropout voltage	I <sub>O</sub> = 150 mA			0.6	V
Output noise voltage	f = 10 Hz to 100 kHz		500		μV
	I <sub>O</sub> = 150 mA		10	12	
Input bias current	$V_I = 6 \text{ V to } 26 \text{ V}, \qquad I_O = 10 \text{ mA}, \qquad T_J = T_J(\text{min}) \text{ to } 125^{\circ}\text{C}$		1	2	mA
	ENABLE > 2 V			0.5	

 $<sup>\</sup>S$  Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1- $\mu$ F capacitor across the input and a 10- $\mu$ F capacitor, with equivalent series resistance of less than 0.4  $\Omega$ , across the output.

NOTE 4: For TL750L05Q/TL751L05Q, all characteristics are measured with a 0.1-μF tantalum capacitor on the output with equivalent series resistance within the guidelines shown in Figure 4.



<sup>‡</sup> Full range is 0°C to 125°C for the TL75xLxxC devices, and -40°C to 125°C for the TL75L05Q devices.

 $<sup>\</sup>P$  T<sub>J</sub>(min) is 0°C for the TL75xLxxC devices, and -40°C for the TL75xLxxQ devices.

### TL750L, TL751L SERIES LOW-DROPOUT VOLTAGE REGULATORS

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# electrical characteristics, $V_I = 14 \text{ V}$ , $I_O = 10 \text{ mA}$ , $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS†	TL750L08 TL751L08			UNIT
		MIN	TYP	MAX	
Output voltage		7.68	8	8.32	V
Output voltage	$T_J = 0$ °C to 125°C	7.6		8.4	V
Input regulation valtage	V <sub>I</sub> = 10 V to 17 V		10	20	mV
Input regulation voltage	V <sub>I</sub> = 9 V to 26 V		25	50	IIIV
Ripple rejection	V <sub>I</sub> = 11 V to 21 V, f = 120 Hz	60	65		dB
Output regulation voltage	I <sub>O</sub> = 5 mA to 150 mA		40	80	mV
Dropout voltage	$I_O = 10 \text{ mA}$			0.2	V
Dropout voltage	I <sub>O</sub> = 150 mA			0.6	V
Output noise voltage	f = 10 Hz to 100 kHz		500		μV
	I <sub>O</sub> = 150 mA		10	12	
Input bias current	$V_{I} = 9 \text{ V to } 26 \text{ V}, \qquad I_{O} = 10 \text{ mA}, \qquad T_{J} = 0^{\circ}\text{C to } 125^{\circ}\text{C}$		1	2	mA
	ENABLE > 2 V			0.5	

TPulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1-µF capacitor across the input and a 10-µF capacitor, with equivalent series resistance of less than 0.4  $\Omega$ , across the output.

# electrical characteristics, $V_I = 14 \text{ V}$ , $I_O = 10 \text{ mA}$ , $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS <sup>†</sup>		TL750L10 TL751L10		
		MIN	TYP	MAX	
Output voltage		9.6	10	10.4	V
Output voltage	$T_J = 0$ °C to 125°C	9.5		10.5	V
Input regulation voltage	V <sub>I</sub> = 12 V to 19 V		10	25	mV
Input regulation voltage	V <sub>I</sub> = 11 V to 26 V		30	60	IIIV
Ripple rejection	$V_{I} = 12 \text{ V to } 22 \text{ V}, \qquad f = 120 \text{ Hz}$	60	65		dB
Output regulation voltage	$I_O = 5 \text{ mA to } 150 \text{ mA}$		50	100	mV
Dropout voltage	$I_O = 10 \text{ mA}$			0.2	V
Dropout voltage	I <sub>O</sub> = 150 mA			0.6	V
Output noise voltage	f = 10 Hz to 100 kHz		700		μV
	I <sub>O</sub> = 150 mA		10	12	
Input bias current	$V_{I} = 11 \text{ V to } 26 \text{ V}, \qquad I_{O} = 10 \text{ mA}, \qquad T_{J} = 0^{\circ}\text{C to } 125^{\circ}\text{C}$		1	2	mA
	ENABLE > 2 V			0.5	

<sup>†</sup> Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1-µF capacitor across the input and a 10-µF capacitor, with equivalent series resistance of less than 0.4  $\Omega$ , across the output.

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# electrical characteristics, $V_I$ = 14 V, $I_O$ = 10 mA, $T_J$ = 25°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS <sup>†</sup>		TL750L12 TL751L12		
		MIN	TYP	MAX	
Output voltage		11.52	12	12.48	V
Output voltage	T <sub>J</sub> = 0°C to 125°C	11.4		12.6	V
lanut regulation valtage	V <sub>I</sub> = 14 V to 19 V		15	30	mV
Input regulation voltage	V <sub>I</sub> = 13 V to 26 V		20	40	IIIV
Ripple rejection	V <sub>I</sub> = 13 V to 23 V, f = 120 Hz	50	55		dB
Output regulation voltage	$I_O = 5$ mA to 150 mA		50	120	mV
Drangut voltage	$I_O = 10 \text{ mA}$			0.2	V
Dropout voltage	I <sub>O</sub> = 150 mA			0.6	V
Output noise voltage	f = 10 Hz to 100 kHz		700		μV
Input bias current	I <sub>O</sub> = 150 mA		10	12	
	$V_{I} = 13 \text{ V to } 26 \text{ V},  I_{O} = 10 \text{ mA},  T_{J} = 0^{\circ}\text{C to } 125^{\circ}\text{C}$		1	2	mA
	ENABLE > 2 V			0.5	

<sup>†</sup> Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1- $\mu$ F capacitor across the input and a 10- $\mu$ F capacitor, with equivalent series resistance of less than 0.4  $\Omega$ , across the output.

# electrical characteristics, $V_I = 14 \text{ V}$ , $I_O = 10 \text{ mA}$ , $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER		TL	UNIT		
PARAMETER	TEST CONDITIONS†	MIN	TYP	MAX	UNIT
Output voltage			5		V
Input regulation voltage	V <sub>I</sub> = 9 V to 16 V		5		mV
	$V_I = 6 \text{ V to } 26 \text{ V}$		6		IIIV
Ripple rejection	V <sub>I</sub> = 8 V to 18 V, f = 120 Hz		65		dB
Output regulation voltage	I <sub>O</sub> = 5 mA to 150 mA		20		mV
Output noise voltage	f = 10 Hz to 100 kHz		500		μV
Input bias current	I <sub>O</sub> = 150 mA		10		mΛ
	$V_I = 6 \text{ V to } 26 \text{ V}, \qquad I_O = 10 \text{ mA}$		1		mA

<sup>†</sup> Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1- $\mu$ F capacitor across the input and a 10- $\mu$ F capacitor, with equivalent series resistance of less than 0.4  $\Omega$ , across the output.

# TL750L, TL751L SERIES LOW-DROPOUT VOLTAGE REGULATORS

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# electrical characteristics, $V_I$ = 14 V, $I_O$ = 10 mA, $T_J$ = 25°C (unless otherwise noted)

PARAMETER	TEST SOMBITIONS!	TL750L08	UNIT	
FARAINETER	TEST CONDITIONS†	MIN TYP	MAX	UNIT
Output voltage		8		V
Input regulation voltage	V <sub>I</sub> = 10 V to 17 V	10		mV
Input regulation voltage	V <sub>I</sub> = 9 V to 26 V	25		IIIV
Ripple rejection	$V_{I} = 11 \text{ V to } 21 \text{ V}, \qquad f = 120 \text{ Hz}$	65		dB
Output regulation voltage	I <sub>O</sub> = 5 mA to 150 mA	40		mV
Output noise voltage	f = 10 Hz to 100 kHz	500		μV
Input bias current	I <sub>O</sub> = 150 mA	10		mA
	$V_I = 9 \text{ V to } 26 \text{ V}, \qquad I_O = 10 \text{ mA}$	1		IIIA

<sup>†</sup> Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1- $\mu$ F capacitor across the input and a 10- $\mu$ F capacitor, with equivalent series resistance of less than 0.4  $\Omega$ , across the output.

#### electrical characteristics, $V_I = 14 \text{ V}$ , $I_O = 10 \text{ mA}$ , $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS†	TL750L10Y	UNIT	
FARAIMETER	TEST CONDITIONS!	MIN TYP MAX	UNIT	
Output voltage		10	V	
Input regulation voltage	V <sub>I</sub> = 12 V to 19 V	10	mV	
Input regulation voltage	V <sub>I</sub> = 11 V to 26 V	30	IIIV	
Ripple rejection	V <sub>I</sub> = 12 V to 22 V, f = 120 Hz	65	dB	
Output regulation voltage	I <sub>O</sub> = 5 mA to 150 mA	50	mV	
Output noise voltage	f = 10 Hz to 100 kHz	700	μV	
Input bias current	I <sub>O</sub> = 150 mA	10	m /	
	$V_I = 11 \text{ V to 26 V}, \qquad I_O = 10 \text{ mA}$	1	mA	

<sup>†</sup> Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1- $\mu$ F capacitor across the input and a 10- $\mu$ F capacitor, with equivalent series resistance of less than  $0.4~\Omega$ , across the output.

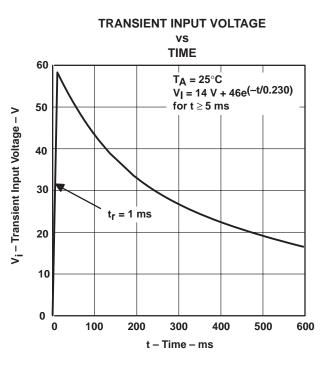
#### electrical characteristics, V<sub>I</sub> = 14 V, I<sub>O</sub> = 10 mA, T<sub>J</sub> = 25°C (unless otherwise noted)

PARAMETER	TEST SOMBITIONS!	TL750L12Y	UNIT
FARAINETER	TEST CONDITIONS†	MIN TYP MAX	UNIT
Output voltage		12	V
Input regulation voltage	V <sub>I</sub> = 14 V to 19 V	15	mV
Input regulation voltage	V <sub>I</sub> = 13 V to 26 V	20	IIIV
Ripple rejection	V <sub>I</sub> = 13 V to 23 V, f = 120 Hz	55	dB
Output regulation voltage	I <sub>O</sub> = 5 mA to 150 mA	50	mV
Output noise voltage	f = 10 Hz to 100 kHz	700	μV
Input bias current	I <sub>O</sub> = 150 mA	10	mA
	$V_I = 13 \text{ V to } 26 \text{ V}, \qquad I_O = 10 \text{ mA}$	1	IIIA

<sup>†</sup> Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1- $\mu$ F capacitor across the input and a 10- $\mu$ F capacitor, with equivalent series resistance of less than  $0.4~\Omega$ , across the output.



#### **TYPICAL CHARACTERISTICS**



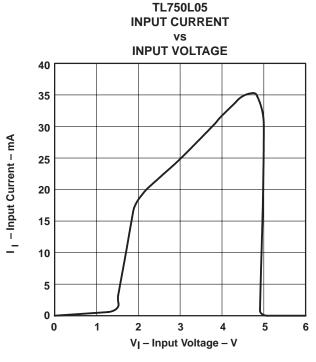


Figure 1

Figure 2

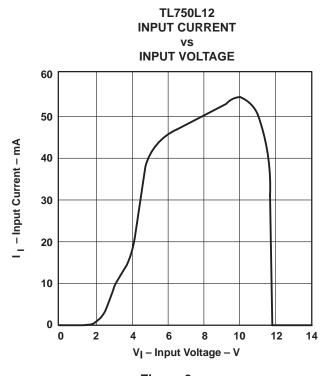


Figure 3

#### TYPICAL CHARACTERISTICS

# TL750L05 EQUIVALENT SERIES RESISTANCE vs

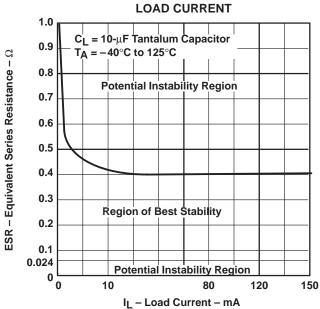


Figure 4

#### **IMPORTANT NOTICE**

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